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Substitute Form PTO-1449 (Modified) 0 2 2002

U.S. Department of Commerce Patent and Trademark Office

Attomey's Docket No. 07043-103001

Application No. 09/994,280

Substitute Disclosure Form (PTO-1449)

ฝึกformation Disclosure Statement by Applicant
(Use several sheets if necessary)

Applicant

George M. Dougherty

Filing Date

Group Art Unit 2812

MM

November 26, 2001

**U.S. Patent Documents** Examiner Desig. Patent Filing Date If Appropriate Initial ID Number Issue Date Patentee Class Subclass 03/07/94 07/29/1997 Keller et al. AA5,651,900 216 56 500.21 AB 4,801,380 01/31/1989 Parket et al. 210 12/23/87 AC AD ΑE AF AG ΑH ΑI ΑJ ΑK

Foreign Patent Documents or Published Foreign Patent Applications								
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	Other Documents (include Author, Title, Date, and Place of Publication)						
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RUN	AQ	Wen-Hwa Chu; Ferrari, M.; "Silicon Nanofilter with Absolute Pore Size and High Mechanical Strength"; 1995; SPIE-Int. Soc. Opt. Eng., Vol. 2593, p. 9-20					
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